

1      Claim 4 (amended):

2      The device according to claim 3, wherein the substrate can be maintained at elevated  
3      temperatures during transition from MOVPE to HVPE.

1      Claim 5 (amended):

2      The device according to claim 2, wherein said device can also transition from HVPE to  
3      MOVPE *in situ*.

1      Claim 6 (amended): The device according to claim 5, wherein said device can also  
2      transition from HVPE to MOVPE *in situ*.

1      Claim 7 (amended):

2      The device according to claim 6, wherein the substrate can be maintained at elevated  
3      temperatures during transition from HVPE to MOVPE.

1      Claim 8 (amended):

2      The device according to claim 1, wherein said device can be used to grow a  
3      III-V nitride compound semiconductor onto the surface of the substrate.

1      Claim 9 (amended): The device according to claim 8, wherein said device can be used  
2      to grow GaN onto the surface of the substrate.

1      Claim 10 (amended):

2      The device according to claim 9, wherein said means for performing HVPE comprises  
3      a hot wall reactor having a source zone, and  
4      a downstream mixing zone,

5      wherein TMG can be reacted with HCl in the source zone to form a chlorinated gallium  
6      species, and wherein the chlorinated gallium species can combine with NH<sub>3</sub> in the downstream  
7      mixing zone and directed toward the substrate for deposition of GaN onto the substrate.

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Claim 11 (amended):

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The device according to claim 9, wherein said means for performing MOVPE comprises

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a low pressure ~~horizontal~~ cold-wall MOCVD reactor.<sup>horizontal</sup>  
horizontal